Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies.

- Blocking Voltage to 400 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Four Quadrant Gating
- Device Marking: Logo, Device Type, e.g., T2800D, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage ⁽¹⁾ (T _J = -40 to +125°C, Gate Open)	V _{DRM} , V _{RRM}	400	Volts
On–State RMS Current (All Conduction Angles, T _C = +80°C)	I _{T(RMS)}	8.0	Amps
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, TJ = +80°C)	ITSM	100	Amps
Circuit Fusing Consideration (t = 8.3 ms)	l ² t	40	A ² s
Peak Gate Power (Pulse Width = 10 μs, T _C = +80°C)	Рдм	16	Watts
Average Gate Power (t = 8.3 ms, $T_C = +80^{\circ}C$)	PG(AV)	0.35	Watt
Peak Gate Current (Pulse Width = 10 μs, T _C = +80°C)	IGM	4.0	Amps
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

⁽¹⁾ VDRM and VRRM for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

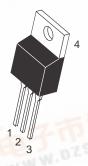


ON Semiconductor

http://onsemi.com

TRIACS 8 AMPERES RMS 400 VOLTS





TO-220AB CASE 221A STYLE 4

PIN ASSIGNMENT		
1	Main Terminal 1	
2	Main Terminal 2	
3	Gate	
4	Main Terminal 2	

ORDERING INFORMATION

Device	Package	Shipping
T2800D	TO220AB	500/Box



THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	2.2	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted; Electricals apply in both directions)

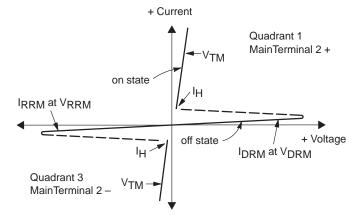
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•	
Peak Repetitive Blocking Current (V_D = Rated V_{DRM} , V_{RRM} ; Gate Open) $T_C = 25^{\circ}C$ $T_C = 100^{\circ}C$	I _{DRM} , IRRM		=	10 2.0	μA mA
ON CHARACTERISTICS		•			•
Peak On-State Voltage ⁽¹⁾ (I _T = \pm 30 A Peak)	VTM	_	1.7	2.0	Volts
Gate Trigger Current (Continuous dc) (V _D = 12 Vdc, R _L = 100 Ohms) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	I _{GT}	_ _ _ _	10 20 15 30	25 60 25 60	mA
Gate Trigger Voltage (Continuous dc) (All Quadrants) (VD = 12 Vdc, RL = 100 Ohms)	V _{GT}	_	1.25	2.5	Volts
Gate Non-Trigger Voltage (Continuous dc) (V _D = 12 V, R _L = 100 Ohms, T _C = 100°C)	V _{GD}	0.2	_	_	Volts
Holding Current (V _D = 12 Vdc, Initiating Current = ±200 mA, Gate Open)	lН	_	15	30	mA
Gate Controlled Turn-On Time $(V_D = Rated\ V_{DRM},\ I_T = 10\ A,\ I_{GT} = 80\ mA,\ Rise\ Time = 0.1\ \mu s)$	^t gt		1.6	_	μs
DYNAMIC CHARACTERISTICS				•	•
Critical Rate-of-Rise of Commutation Voltage ($V_D = Rated\ V_{DRM},\ I_{T(RMS)} = 8\ A$, Commutating di/dt = 4.1 A/ms, Gate Unenergized, $T_C = 80^{\circ}C$)	dv/dt(c)		10	_	V/µs
Critical Rate-of-Rise of Off-State Voltage (VD = Rated VDRM, Exponential Voltage Rise, Gate Open, TC = 100°C)	dv/dt	60	_	_	V/µs

⁽¹⁾ Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

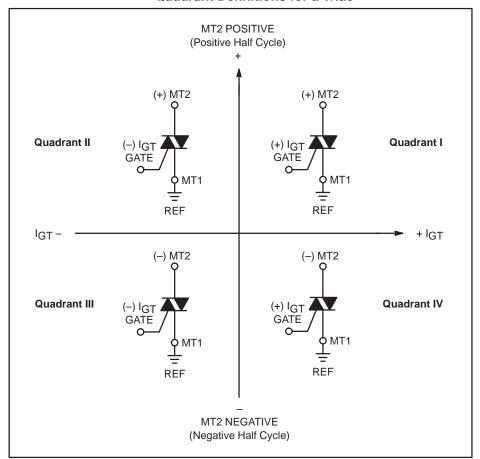
T2800D

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
VDRM	Peak Repetitive Forward Off State Voltage
IDRM	Peak Forward Blocking Current
VRRM	Peak Repetitive Reverse Off State Voltage
IRRM	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
lΗ	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

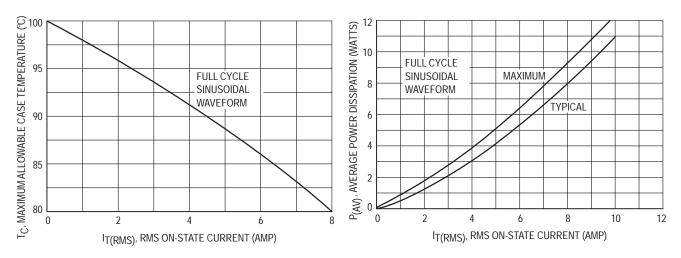
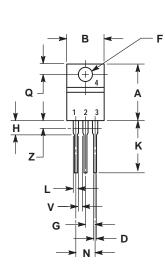


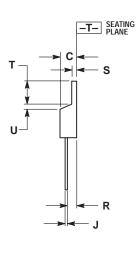
Figure 1. Current Derating

Figure 2. Power Dissipation

PACKAGE DIMENSIONS

TO-220AB CASE 221A-07 ISSUE Z





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

- STYLE 4:
 PIN 1. MAIN TERMINAL 1
 2. MAIN TERMINAL 2
 3. GATE
 4. MAIN TERMINAL 2

Notes

Notes

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